

METHOD OF REUSING PEELED WAFER AND WAFER TO BE REUSED

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Abstract

PROBLEM TO BE SOLVED: To provide a method for actually reusing a peeled wafer as silicon wafer, improve the productivity of SOI wafer, and reduce its cost by performing an appropriate reprocessing to the peeled wafer which is a by-product of a hydrogen-ion peeling method.

SOLUTION: In a method of reusing a peeled wafer as a silicon wafer, by performing an reprocessing to the peeled wafer which is a by-product produced during manufacturing SOI wafers by a hydrogen-ion peeling method, as reprocessing, a surface oxide film 3 is removed (B), and a donor killer heat treatment is performed (D), next polishing is performed to remove steps on the periphery (E), and finally finish polishing is performed (F), which allows the peeled wafer to be reused.

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